Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	67
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	40K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 3.6V
Data Converters	A/D 26x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc560p50l3beaby

Contents

List of figures

1.5.9 Frequency-modulated phase-locked loop (FMPLL)

The FMPLL allows the user to generate high speed system clocks from a 4–40 MHz input clock. Further, the FMPLL supports programmable frequency modulation of the system clock. The PLL multiplication factor, output clock divider ratio are all software configurable.

The PLL has the following major features:

- Input clock frequency: 4–40 MHz
- Maximum output frequency: 64 MHz
- Voltage controlled oscillator (VCO)—frequency 256–512 MHz
- Reduced frequency divider (RFD) for reduced frequency operation without forcing the PLL to relock
- Frequency-modulated PLL
  - Modulation enabled/disabled through software
  - Triangle wave modulation
- Programmable modulation depth (±0.25% to ±4% deviation from center frequency): programmable modulation frequency dependent on reference frequency
- Self-clocked mode (SCM) operation

1.5.10 Main oscillator

The main oscillator provides these features:

- Input frequency range: 4–40 MHz
- Crystal input mode or oscillator input mode
- PLL reference

1.5.11 Internal RC oscillator

This device has an RC ladder phase-shift oscillator. The architecture uses constant current charging of a capacitor. The voltage at the capacitor is compared by the stable bandgap reference voltage.

The RC oscillator provides these features:

- Nominal frequency 16 MHz
- ±5% variation over voltage and temperature after process trim
- Clock output of the RC oscillator serves as system clock source in case loss of lock or loss of clock is detected by the PLL
- RC oscillator is used as the default system clock during startup

1.5.12 Periodic interrupt timer (PIT)

The PIT module implements these features:

- 4 general purpose interrupt timers
- 32-bit counter resolution
- Clocked by system clock frequency
- Each channel can be used as trigger for a DMA request

1.5.24 Deserial serial peripheral interface (DSPI)

The deserial serial peripheral interface (DSPI) module provides a synchronous serial interface for communication between the SPC560P44Lx, SPC560P50Lx MCU and external devices.

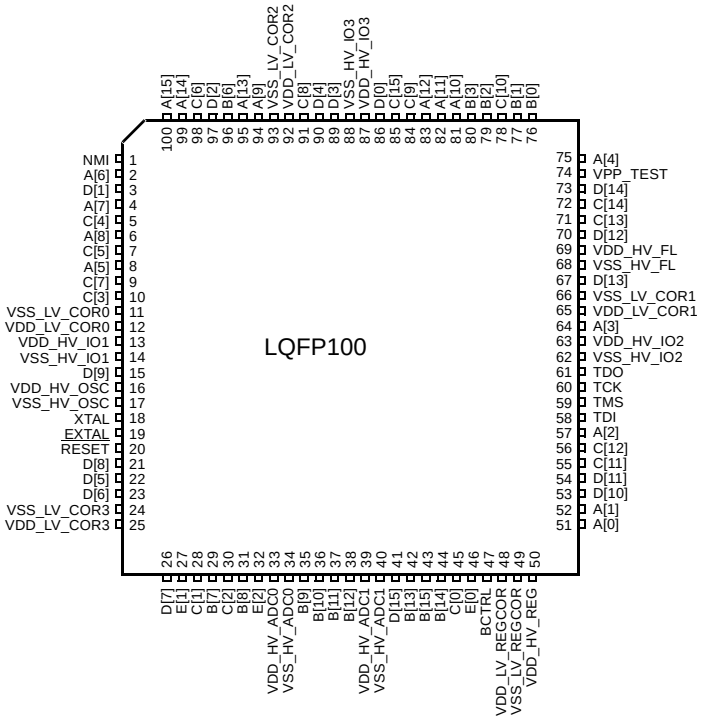
The DSPI modules provide these features:

- Full duplex, synchronous transfers
- Master or slave operation
- Programmable master bit rates
- Programmable clock polarity and phase
- End-of-transmission interrupt flag
- Programmable transfer baud rate
- Programmable data frames from 4 to 16 bits
- Up to 20 chip select lines available
  - 8 on DSPI_0
  - 4 each on DSPI_1, DSPI_2 and DSPI_3
- 8 clock and transfer attributes registers
- Chip select strobe available as alternate function on one of the chip select pins for deglitching
- FIFOs for buffering as many as 5 transfers on the transmit and receive side
- Queueing operation possible through use of the eDMA
- General purpose I/O functionality on pins when not used for SPI

1.5.25 Pulse width modulator (FlexPWM)

The pulse width modulator module (PWM) contains four PWM submodules, each capable of controlling a single half-bridge power stage. There are also four fault channels.

This PWM is capable of controlling most motor types: AC induction motors (ACIM), permanent magnet AC motors (PMAC), both brushless (BLDC) and brush DC motors (BDC), switched (SRM) and variable reluctance motors (VRM), and stepper motors.



Note: Availability of port pin alternate functions depends on product selection.

Figure 4. 100-pin LQFP pinout – Full featured configuration (top view)

2.2 Pin description

The following sections provide signal descriptions and related information about the functionality and configuration of the SPC560P44Lx, SPC560P50Lx devices.

2.2.1 Power supply and reference voltage pins

Table 5 lists the power supply and reference voltage for the SPC560P44Lx, SPC560P50Lx devices.

Table 7. Pin muxing (continued)

Port pin	Pad configuration register (PCR)	Alternate function[1], [2]	Functions	Peripheral[3]	I/O direction [4]	Pad speed[5]		Pin No.	
						SRC = 0	SRC = 1	100-pin	144-pin
A[7]	PCR[7]	ALT0 ALT1 ALT2 ALT3 —	GPIO[7] SOUT — — EIRQ[7]	SIUL DSPI_1 — — SIUL	I/O O — — I	Slow	Medium	4	10
A[8]	PCR[8]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[8] — — — SIN EIRQ[8]	SIUL — — — DSPI_1 SIUL	I/O — — — I I	Slow	Medium	6	12
A[9]	PCR[9]	ALT0 ALT1 ALT2 ALT3 —	GPIO[9] CS1 — B[3] FAULT[0]	SIUL DSPI_2 — FlexPWM_0 FlexPWM_0	I/O O — O I	Slow	Medium	94	134
A[10]	PCR[10]	ALT0 ALT1 ALT2 ALT3 —	GPIO[10] CS0 B[0] X[2] EIRQ[9]	SIUL DSPI_2 FlexPWM_0 FlexPWM_0 SIUL	I/O I/O O I/O I	Slow	Medium	81	118
A[11]	PCR[11]	ALT0 ALT1 ALT2 ALT3 —	GPIO[11] SCK A[0] A[2] EIRQ[10]	SIUL DSPI_2 FlexPWM_0 FlexPWM_0 SIUL	I/O I/O O O I	Slow	Medium	82	120
A[12]	PCR[12]	ALT0 ALT1 ALT2 ALT3 —	GPIO[12] SOUT A[2] B[2] EIRQ[11]	SIUL DSPI_2 FlexPWM_0 FlexPWM_0 SIUL	I/O O O O I	Slow	Medium	83	122
A[13]	PCR[13]	ALT0 ALT1 ALT2 ALT3 — — —	GPIO[13] — B[2] — SIN FAULT[0] EIRQ[12]	SIUL — FlexPWM_0 — DSPI_2 FlexPWM_0 SIUL	I/O — O — I I I	Slow	Medium	95	136

Table 7. Pin muxing (continued)

Port pin	Pad configuration register (PCR)	Alternate function[1], [2]	Functions	Peripheral[3]	I/O direction [4]	Pad speed[5]		Pin No.	
						SRC = 0	SRC = 1	100-pin	144-pin
F[5]	PCR[85]	ALT0 ALT1 ALT2 ALT3	GPIO[85] MDO[2] — —	SIUL NEXUS_0 — —	I/O O — —	Slow	Fast	—	5
F[6]	PCR[86]	ALT0 ALT1 ALT2 ALT3	GPIO[86] MDO[1] — —	SIUL NEXUS_0 — —	I/O O — —	Slow	Fast	—	8
F[7]	PCR[87]	ALT0 ALT1 ALT2 ALT3	GPIO[87] MCKO — —	SIUL NEXUS_0 — —	I/O O — —	Slow	Fast	—	19
F[8]	PCR[88]	ALT0 ALT1 ALT2 ALT3	GPIO[88] MSEO1 — —	SIUL NEXUS_0 — —	I/O O — —	Slow	Fast	—	20
F[9]	PCR[89]	ALT0 ALT1 ALT2 ALT3	GPIO[89] MSEO0 — —	SIUL NEXUS_0 — —	I/O O — —	Slow	Fast	—	23
F[10]	PCR[90]	ALT0 ALT1 ALT2 ALT3	GPIO[90] EVTO — —	SIUL NEXUS_0 — —	I/O O — —	Slow	Fast	—	24
F[11]	PCR[91]	ALT0 ALT1 ALT2 ALT3 —	GPIO[91] — — — EVTI	SIUL — — — NEXUS_0	I/O — — — I	Slow	Medium	—	25
F[12]	PCR[92]	ALT0 ALT1 ALT2 ALT3	GPIO[92] ETC[3] — —	SIUL eTimer_1 — —	I/O I/O — —	Slow	Medium	—	106
F[13]	PCR[93]	ALT0 ALT1 ALT2 ALT3	GPIO[92] ETC[4] — —	SIUL eTimer_1 — —	I/O I/O — —	Slow	Medium	—	112

3 Electrical characteristics

3.1 Introduction

This section contains device electrical characteristics as well as temperature and power considerations.

This microcontroller contains input protection against damage due to high static voltages. However, it is advisable to take precautions to avoid application of any voltage higher than the specified maximum rated voltages.

To enhance reliability, unused inputs can be driven to an appropriate logic voltage level (V_{DD} or V_{SS}). This can be done by the internal pull-up or pull-down resistors, which are provided by the device for most general purpose pins.

The following tables provide the device characteristics and its demands on the system.

In the tables where the device logic provides signals with their respective timing characteristics, the symbol “CC” for Controller Characteristics is included in the Symbol column.

In the tables where the external system must provide signals with their respective timing characteristics to the device, the symbol “SR” for System Requirement is included in the Symbol column.

Caution: All of the following parameter values can vary depending on the application and must be confirmed during silicon characterization or silicon reliability trial.

3.2 Parameter classification

The electrical parameters are guaranteed by various methods. To give the customer a better understanding, the classifications listed in *Table 8* are used and the parameters are tagged accordingly in the tables where appropriate.

Table 8. Parameter classifications

Classification tag	Tag description
P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

Note: The classification is shown in the column labeled “C” in the parameter tables where appropriate.

3.3 Absolute maximum ratings

Table 9. Absolute maximum ratings(1)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max(2)	
V_{SS}	SR	Device ground	—	0	0	V
$V_{DD\_HV\_IOx}$(3)	SR	3.3 V / 5.0 V input/output supply voltage with respect to ground (V_{SS})	—	–0.3	6.0	V
$V_{SS\_HV\_IOx}$	SR	Input/output ground voltage with respect to ground (V_{SS})	—	–0.1	0.1	V
$V_{DD\_HV\_FL}$	SR	3.3 V / 5.0 V code and data flash supply voltage with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to $V_{DD\_HV\_IOx}$		$V_{DD\_HV\_IOx}$ + 0.3	
$V_{SS\_HV\_FL}$	SR	Code and data flash ground with respect to ground (V_{SS})	—	–0.1	0.1	V
$V_{DD\_HV\_OSC}$	SR	3.3 V / 5.0 V crystal oscillator amplifier supply voltage with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to $V_{DD\_HV\_IOx}$		$V_{DD\_HV\_IOx}$ + 0.3	
$V_{SS\_HV\_OSC}$	SR	3.3 V / 5.0 V crystal oscillator amplifier reference voltage with respect to ground (V_{SS})	—	–0.1	0.1	V
$V_{DD\_HV\_REG}$	SR	3.3 V / 5.0 V voltage regulator supply voltage with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to $V_{DD\_HV\_IOx}$		$V_{DD\_HV\_IOx}$ + 0.3	
$V_{DD\_HV\_ADC0}$(4)	SR	3.3 V / 5.0 V ADC_0 supply and high reference voltage with respect to ground (V_{SS})	$V_{DD\_HV\_REG}$ < 2.7 V	–0.3	$V_{DD\_HV\_REG}$ + 0.3	V
			$V_{DD\_HV\_REG}$ > 2.7 V		6.0	
$V_{SS\_HV\_ADC0}$	SR	ADC_0 ground and low reference voltage with respect to ground (V_{SS})	—	–0.1	0.1	V
$V_{DD\_HV\_ADC1}$(4)	SR	3.3 V / 5.0 V ADC_0 supply and high reference voltage with respect to ground (V_{SS})	$V_{DD\_HV\_REG}$ < 2.7 V	–0.3	$V_{DD\_HV\_REG}$ + 0.3	V
			$V_{DD\_HV\_REG}$ > 2.7 V		6.0	
$V_{SS\_HV\_ADC1}$	SR	ADC_1 ground and low reference voltage with respect to ground (V_{SS})	—	–0.1	0.1	V
TV_{DD}	SR	Slope characteristics on all V_{DD} during power up(5) with respect to ground (V_{SS})	—	3.0	500 x 10^3 (0.5 [V/µs])	V/s
V_{IN}	SR	Voltage on any pin with respect to ground ($V_{SS\_HV\_IOx}$) with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to $V_{DD\_HV\_IOx}$		$V_{DD\_HV\_IOx}$ + 0.3	

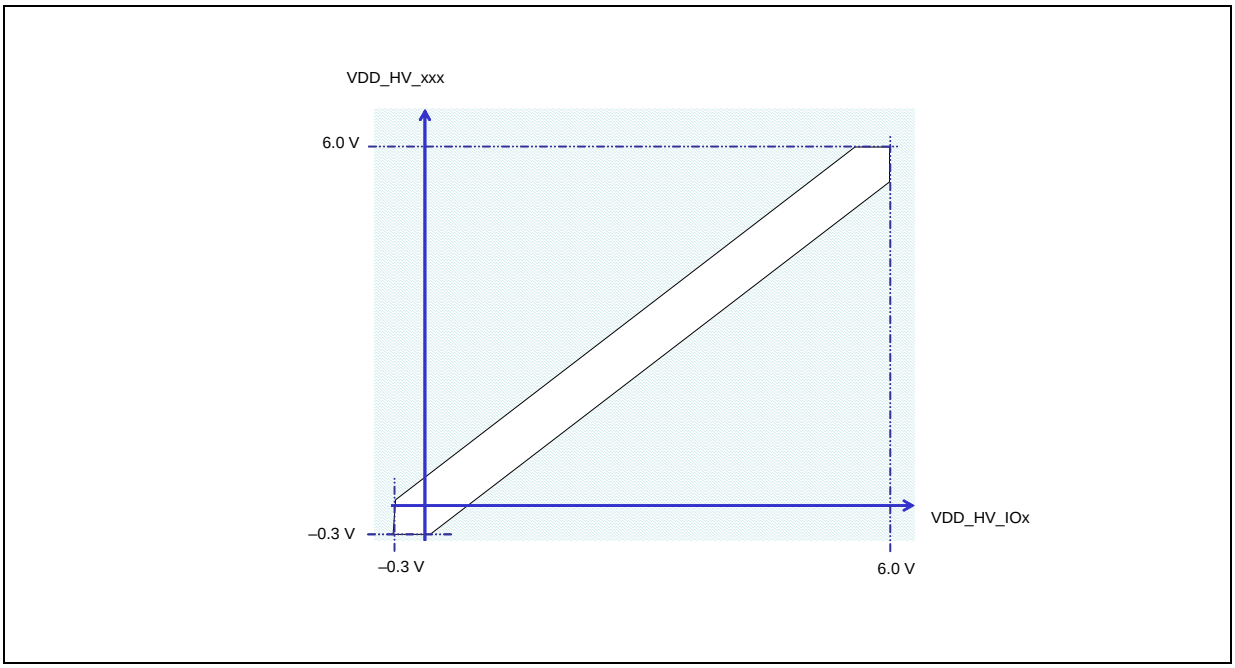


Figure 5. Power supplies constraints (–0.3 V ≤ $V_{DD\_HV\_IOx}$ ≤ 6.0 V)

The SPC560P44Lx, SPC560P50Lx supply architecture allows of having ADC supply managed independently from standard V_{DD_HV} supply. *Figure 6* shows the constraints of the ADC power supply.

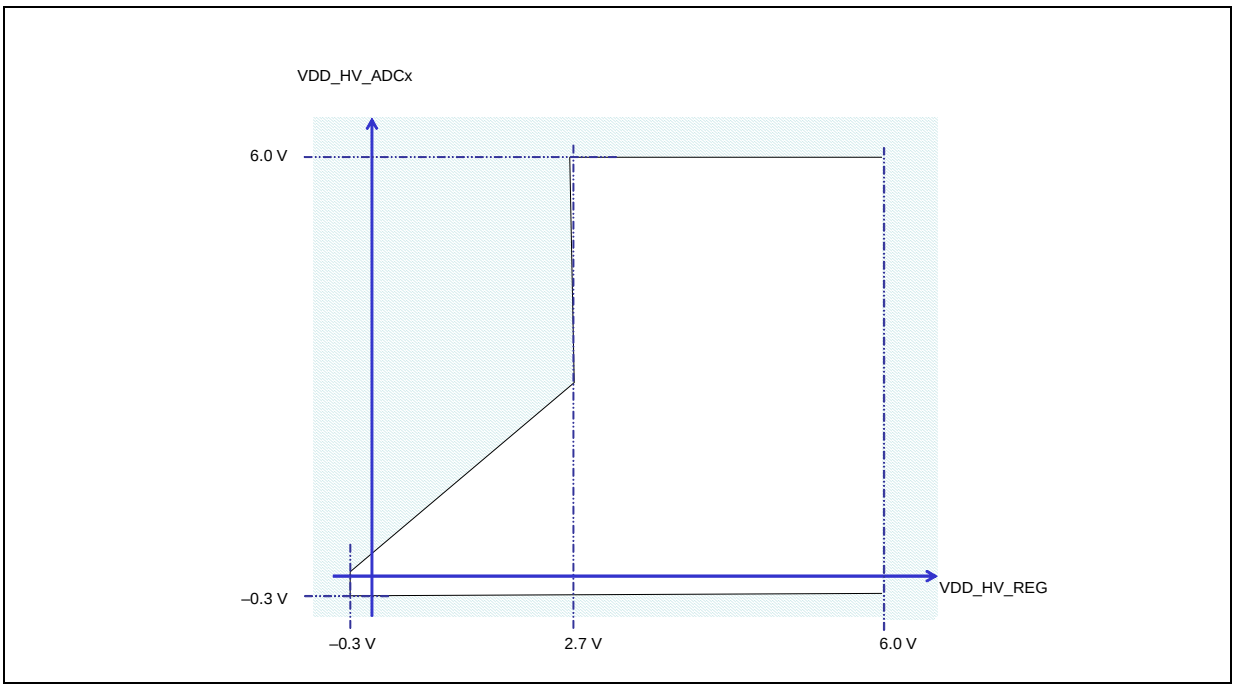


Figure 6. Independent ADC supply (–0.3 V ≤ $V_{DD\_HV\_REG}$ ≤ 6.0 V)

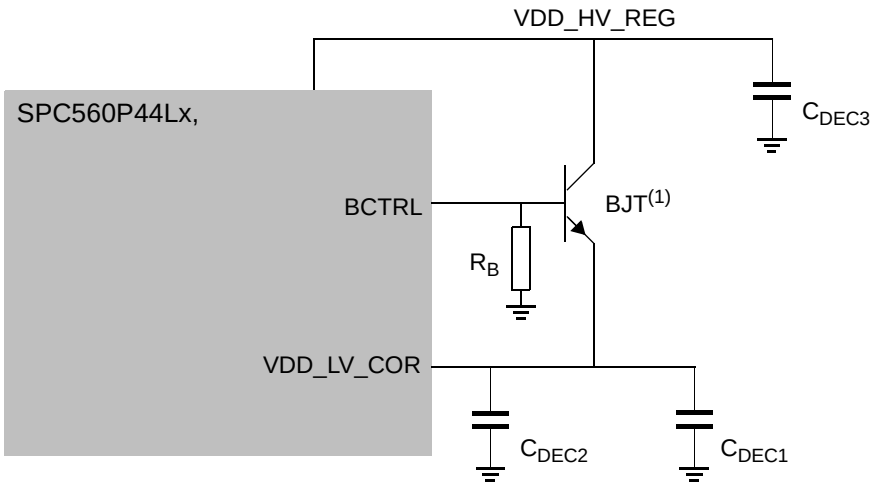
L_{Reg}, see *Table 17*.

Note: The voltage regulator output cannot be used to drive external circuits. Output pins are used only for decoupling capacitances.

$V_{DD\_LV\_COR}$ must be generated using internal regulator and external NPN transistor. It is not possible to provide $V_{DD\_LV\_COR}$ through external regulator.

For the SPC560P44Lx, SPC560P50Lx microcontroller, capacitors, with total values not below C_{DEC1}, should be placed between $V_{DD\_LV\_CORx}/V_{SS\_LV\_CORx}$ close to external ballast transistor emitter. 4 capacitors, with total values not below C_{DEC2}, should be placed close to microcontroller pins between each $V_{DD\_LV\_CORx}/V_{SS\_LV\_CORx}$ supply pairs and the $V_{DD\_LV\_REGCOR}/V_{SS\_LV\_REGCOR}$ pair . Additionally, capacitors with total values not below C_{DEC3}, should be placed between the $V_{DD\_HV\_REG}/V_{SS\_HV\_REG}$ pins close to ballast collector. Capacitors values have to take into account capacitor accuracy, aging and variation versus temperature.

All reported information are valid for voltage and temperature ranges described in recommended operating condition, *Table 10* and *Table 11*.



1. Refer to *Table 16*.

Figure 9. Configuration with resistor on base

Table 16. Approved NPN ballast components (configuration with resistor on base)

Part	Manufacturer	Approved derivatives(1)
BCP68	ON Semi	BCP68
	NXP	BCP68-25
	Infineon	BCP68-25
BCX68	Infineon	BCX68-10;BCX68-16;BCX68-25
BC868	NXP	BC868

Table 16. Approved NPN ballast components (configuration with resistor on base)

Part	Manufacturer	Approved derivatives(1)
BC817	Infineon	BC817-16;BC817-25;BC817SU;
	NXP	BC817-16;BC817-25
BCP56	ST	BCP56-16
	Infineon	BCP56-10;BCP56-16
	ON Semi	BCP56-10
	NXP	BCP56-10;BCP56-16

1. For automotive applications please check with the appropriate transistor vendor for automotive grade certification

Table 17. Voltage regulator electrical characteristics (configuration with resistor on base)

Symbol		C	Parameter	Conditions	Value			Unit
					Min	Typ	Max	
$V_{DD\_LV\_REGCOR}$	CC	P	Output voltage under maximum load run supply current configuration	Post-trimming	1.15	—	1.32	V
R_B	SR	—	External resistance on bipolar junction transistor (BJT) base	—	18	—	22	kΩ
C_{DEC1}	SR	—	External decoupling/stability ceramic capacitor	BJT from *Table 16*. 3 capacitances (i.e. X7R or X8R capacitors) with nominal value of 10 µF	19.5	30	—	µF
				BJT BC817, one capacitance of 22 µF	14.3	22		µF
R_{REG}	SR	—	Resulting ESR of all three capacitors of C_{DEC1}	BJT from *Table 16*. 3x10 µF. Absolute maximum value between 100 kHz and 10 MHz	—	—	50	mΩ
			Resulting ESR of the unique capacitor C_{DEC1}	BJT BC817, 1x 22 µF. Absolute maximum value between 100 kHz and 10 MHz	10	—	40	mΩ
C_{DEC2}	SR	—	External decoupling/stability ceramic capacitor	4 capacitances (i.e. X7R or X8R capacitors) with nominal value of 440 nF	1200	1760	—	nF
C_{DEC3}	SR	—	External decoupling/stability ceramic capacitor on $V_{DD\_HV\_REG}$	3 capacitances (i.e. X7R or X8R capacitors) with nominal value of 10 µF; C_{DEC3} has to be equal or greater than C_{DEC1}	19.5	30	—	µF
L_{Reg}	SR	—	Resulting ESL of $V_{DD\_HV\_REG}$, BCTRL and $V_{DD\_LV\_CORx}$ pins	—	—	—	15	nH

Table 22. Supply current (5.0 V, NVUSRO[PAD3V5V] = 0)

Symbol	C	Parameter		Conditions		Value		Unit
						Typ	Max	
$I_{DD\_LV\_CORx}$	T	Supply current	RUN—Maximum mode(1)	$V_{DD\_LV\_CORx}$ externally forced at 1.3 V	40 MHz	62	77	mA
					64 MHz	71	88	
			RUN—Typical mode(2)		40 MHz	45	56	
					64 MHz	52	65	
	P		RUN—Maximum mode(3)	$V_{DD\_LV\_CORx}$ externally forced at 1.3 V	64 MHz	60	75	
			HALT mode(4)	$V_{DD\_LV\_CORx}$ externally forced at 1.3 V	—	1.5	10	
			STOP mode(5)	$V_{DD\_LV\_CORx}$ externally forced at 1.3 V	—	1	10	
I_{DD_FLASH}	T		Flash during read	$V_{DD\_HV\_FL}$ at 5.0 V	—	10	12	
			Flash during erase operation on 1 flash module	$V_{DD\_HV\_FL}$ at 5.0 V	—	15	19	
I_{DD_ADC}	T		ADC—Maximum mode(1)	$V_{DD\_HV\_ADC0}$ at 5.0 V $V_{DD\_HV\_ADC1}$ at 5.0 V f_{ADC} = 16 MHz	ADC_1	3.5	5	
					ADC_0	3	4	
			ADC—Typical mode(2)		ADC_1	0.8	1	
					ADC_0	0.005	0.006	
I_{DD_OSC}	T		Oscillator	V_{DD_OSC} at 5.0 V	8 MHz	2.6	3.2	

1. Maximum mode: FlexPWM, ADCs, CTU, DSPI, LINFlex, FlexCAN, 15 output pins, 1st and 2nd PLL enabled. I/O supply current excluded.
2. Typical mode configurations: DSPI, LINFlex, FlexCAN, 15 output pins, 1st PLL only. I/O supply current excluded.
3. Code fetched from RAM, PLL_0: 64 MHz system clock (x4 multiplier with 16 MHz XTAL), PLL_1 is ON at PHI_div2 = 120 MHz and PHI_div3 = 80 MHz, auxiliary clock sources set that all peripherals receive maximum frequency, all peripherals enabled.
4. Halt mode configurations: code fetched from RAM, code and data flash memories in low power mode, OSC/PLL_0/PLL_1 are OFF, core clock frozen, all peripherals are disabled.
5. STOP “P” mode Device Under Test (DUT) configuration: code fetched from RAM, code and data flash memories OFF, OSC/PLL_0/PLL_1 are OFF, core clock frozen, all peripherals are disabled.

3.10.3 DC electrical characteristics (3.3 V)

Table 23 gives the DC electrical characteristics at 3.3 V ($3.0\ V < V_{DD\_HV\_IOx} < 3.6\ V$, NVUSRO[PAD3V5V] = 1); see *Figure 14*.

Table 23. DC electrical characteristics (3.3 V, NVUSRO[PAD3V5V] = 1)(1)

Symbol	C	Parameter	Conditions	Value		Unit
				Min	Max	
V_{IL}	D	Low level input voltage	—	–0.1(2)	—	V
	P		—	—	0.35 $V_{DD\_HV\_IOx}$	V

Table 26. I/O weight (continued)

Pad	LQFP144		LQFP100	
	Weight 5V	Weight 3.3V	Weight 5V	Weight 3.3V
PAD[86]	9%	6%	—	—
MODO[0]	12%	8%	—	—
PAD[7]	4%	4%	11%	10%
PAD[36]	5%	4%	11%	9%
PAD[8]	5%	4%	10%	9%
PAD[37]	5%	4%	10%	9%
PAD[5]	5%	4%	9%	8%
PAD[39]	5%	4%	9%	8%
PAD[35]	5%	4%	8%	7%
PAD[87]	12%	9%	—	—
PAD[88]	9%	6%	—	—
PAD[89]	10%	7%	—	—
PAD[90]	15%	11%	—	—
PAD[91]	6%	5%	—	—
PAD[57]	8%	7%	8%	7%
PAD[56]	13%	11%	13%	11%
PAD[53]	14%	12%	14%	12%
PAD[54]	15%	13%	15%	13%
PAD[55]	25%	22%	25%	22%
PAD[96]	27%	24%	—	—
PAD[65]	1%	1%	1%	1%
PAD[67]	1%	1%	—	—
PAD[33]	1%	1%	1%	1%
PAD[68]	1%	1%	—	—
PAD[23]	1%	1%	1%	1%
PAD[69]	1%	1%	—	—
PAD[34]	1%	1%	1%	1%
PAD[70]	1%	1%	—	—
PAD[24]	1%	1%	1%	1%
PAD[71]	1%	1%	—	—
PAD[66]	1%	1%	1%	1%
PAD[25]	1%	1%	1%	1%
PAD[26]	1%	1%	1%	1%

Table 27. I/O consumption (continued)

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
I_{RMSMED}	CC	D	Root medium square I/O current for MEDIUM configuration	C_L = 25 pF, 13 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	6.6	mA
				C_L = 25 pF, 40 MHz		—	—	13.4	
				C_L = 100 pF, 13 MHz		—	—	18.3	
				C_L = 25 pF, 13 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	5	
				C_L = 25 pF, 40 MHz		—	—	8.5	
				C_L = 100 pF, 13 MHz		—	—	11	
I_{RMSFST}	CC	D	Root medium square I/O current for FAST configuration	C_L = 25 pF, 40 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	22	mA
				C_L = 25 pF, 64 MHz		—	—	33	
				C_L = 100 pF, 40 MHz		—	—	56	
				C_L = 25 pF, 40 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	14	
				C_L = 25 pF, 64 MHz		—	—	20	
				C_L = 100 pF, 40 MHz		—	—	35	
I_{AVGSEG}	SR	D	Sum of all the static I/O current within a supply segment	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0		—	—	70	mA
				V_{DD} = 3.3 V ± 10%, PAD3V5V = 1		—	—	65	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified
2. Stated maximum values represent peak consumption that lasts only a few ns during I/O transition.

3.11 Main oscillator electrical characteristics

The SPC560P44Lx, SPC560P50Lx provides an oscillator/resonator driver.

Table 28. Main oscillator output electrical characteristics (5.0 V, NVUSRO[PAD3V5V] = 0)

Symbol		C	Parameter	Value		Unit
				Min	Max	
f_{OSC}	SR	—	Oscillator frequency	4	40	MHz
g_m	—	P	Transconductance	6.5	25	mA/V
V_{OSC}	—	T	Oscillation amplitude on XTAL pin	1	—	V
t_{OSCSU}	—	T	Start-up time[1],[2]	8	—	ms

1. The start-up time is dependent upon crystal characteristics, board leakage, etc., high ESR and excessive capacitive loads can cause long start-up time.
2. Value captured when amplitude reaches 90% of XTAL

A second aspect involving the capacitance network shall be considered. Assuming the three capacitances C_F, C_{P1} and C_{P2} are initially charged at the source voltage V_A (refer to the equivalent circuit reported in *Figure 16*): A charge sharing phenomenon is installed when the sampling phase is started (A/D switch closed).

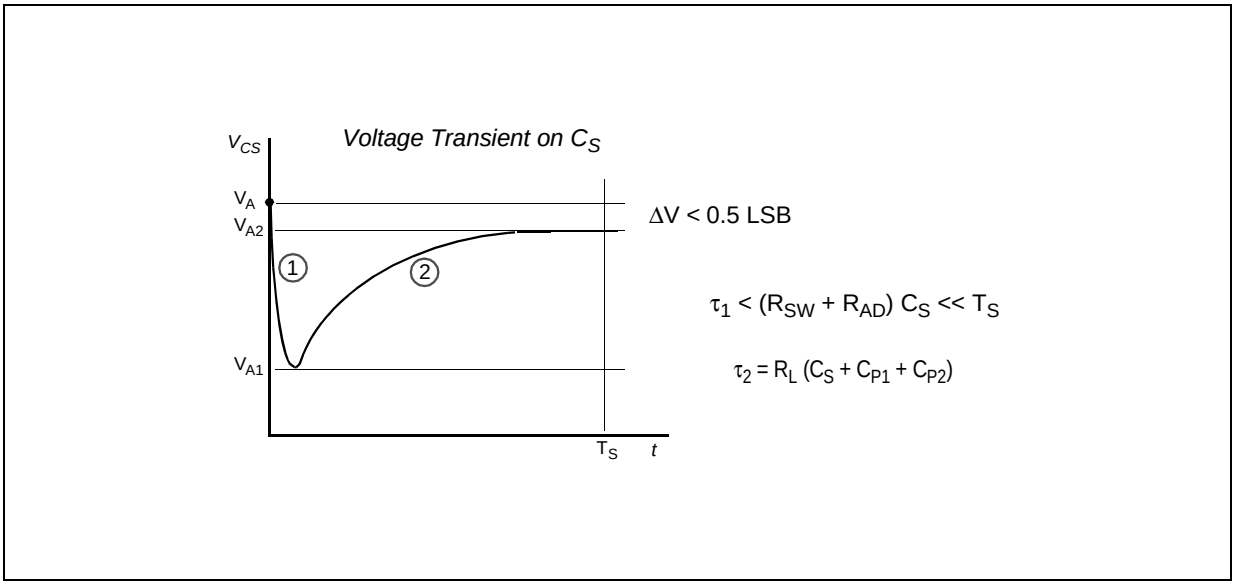


Figure 17. Transient behavior during sampling phase

In particular two different transient periods can be distinguished:

- A first and quick charge transfer from the internal capacitance C_{P1} and C_{P2} to the sampling capacitance C_S occurs (C_S is supposed initially completely discharged): considering a worst case (since the time constant in reality would be faster) in which C_{P2} is reported in parallel to C_{P1} (call $C_P = C_{P1} + C_{P2}$), the two capacitances C_P and C_S are in series, and the time constant is

Equation 5

$$\tau_1 = (R_{SW} + R_{AD}) \bullet \frac{C_P \bullet C_S}{C_P + C_S}$$

Equation 5 can again be simplified considering only C_S as an additional worst condition. In reality, the transient is faster, but the A/D converter circuitry has been designed to be robust also in the very worst case: the sampling time T_S is always much longer than the internal time constant:

Equation 6

$$\tau_1 < (R_{SW} + R_{AD}) \bullet C_S \ll T_S$$

The charge of C_{P1} and C_{P2} is redistributed also on C_S, determining a new value of the voltage V_{A1} on the capacitance according to *Equation 7*:

3.15 Flash memory electrical characteristics

Table 34. Program and erase specifications

Symbol	C	Parameter	Value				Unit
			Min	Typical(1)	Initial max(2)	Max(3)	
$T_{dwprogram}$	P	Double Word (64 bits) Program Time(4)	—	22	50	500	µs
T_{BKPRG}	P	Bank Program (512 KB)(4)(5)	—	1.45	1.65	33	s
	P	Bank Program (64 KB)(4)(5)	—	0.18	0.21	4.10	s
$T_{16kpperase}$	P	16 KB Block Pre-program and Erase Time	—	300	500	5000	ms
$T_{32kpperase}$	P	32 KB Block Pre-program and Erase Time	—	400	600	5000	ms
$T_{128kpperase}$	P	128 KB Block Pre-program and Erase Time	—	800	1300	7500	ms

1. Typical program and erase times assume nominal supply values and operation at 25 °C. All times are subject to change pending device characterization.
2. Initial factory condition: < 100 program/erase cycles, 25 °C, typical supply voltage.
3. The maximum program and erase times occur after the specified number of program/erase cycles. These maximum values are characterized but not guaranteed.
4. Actual hardware programming times. This does not include software overhead.
5. Typical Bank programming time assumes that all cells are programmed in a single pulse. In reality some cells will require more than one pulse, adding a small overhead to total bank programming time (see Initial Max column).

Table 35. Flash memory module life

Symbol	C	Parameter	Conditions	Value		Unit
				Min	Typ	
P/E	C	Number of program/erase cycles per block for 16 KB blocks over the operating temperature range (T_J)	—	100000	—	cycles
P/E	C	Number of program/erase cycles per block for 32 KB blocks over the operating temperature range (T_J)	—	10000	100000	cycles
P/E	C	Number of program/erase cycles per block for 128 KB blocks over the operating temperature range (T_J)	—	1000	100000	cycles
Retention	C	Minimum data retention at 85 °C average ambient temperature(1)	Blocks with 0–1000 P/E cycles	20	—	years
			Blocks with 10000 P/E cycles	10	—	years
			Blocks with 100000 P/E cycles	5	—	years

1. Ambient temperature averaged over duration of application, not to exceed recommended product operating temperature range.

5 Ordering information

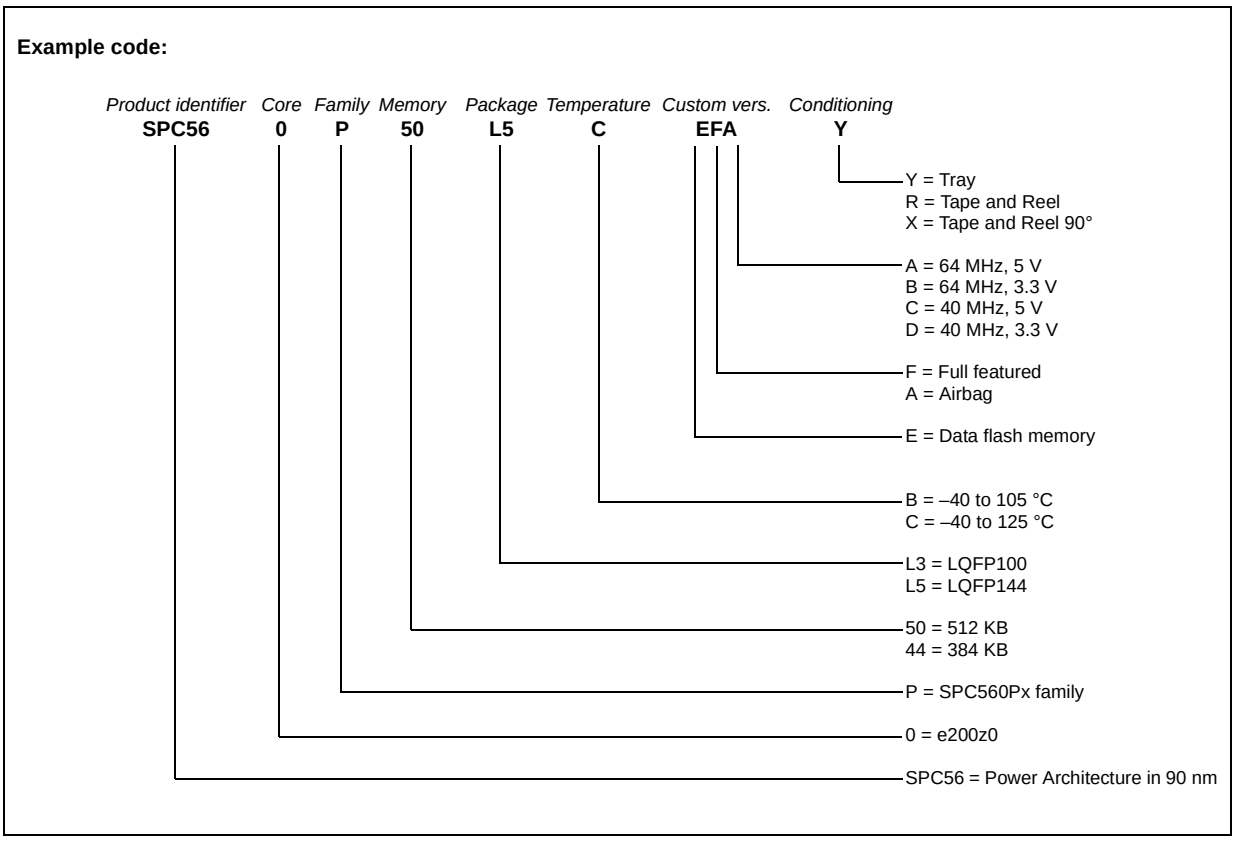


Figure 40. Commercial product code structure[(a)]

a. Not all configurations are available on the market. Please contact your ST sales representative to get the list of orderable commercial part number.

Table 46. Revision history (continued)

Date	Revision	Changes
18-Jul-2012	8	Updated *Table 1 (Device summary)* *Section 1.5.4, Flash memory*: Changed “Data flash memory: 32-bit ECC” to “Data flash memory: 64-bit ECC” *Figure 40 (Commercial product code structure)*, replaced "C = 60 MHz, 5 V" and "D = 60 MHz, 3.3 V" with respectively "C = 40 MHz, 5 V" and "D = 40 MHz, 3.3 V" *Table 9 (Absolute maximum ratings)*, updated TV_{DD} parameter, the minimum value to 3.0 V/s and the maximum value to 0.5 V/µs *Table 7 (Pin muxing)*, changed the description in the column "I/O direction" from "I/O" to "O" for the following port pins: A[10] with function B[0] A[11] with function A[0] A[11] with function A[2] A[12] with function A[2] A[12] with function B[2] A[13] with function B[2] C[7] with function A[1] C[10] with function A[3] C[15] with function A[1] D[0] with function B[1] D[10] with function A[0] D[11] with function B[0] D[13] with function A[1] D[14] with function B[1] Updated *Section 3.8.1, Voltage regulator electrical characteristics* Added *Table 27 (I/O consumption)* *Section 3.10, DC electrical characteristics*: deleted references to “oscillator margin” deleted subsection “NVUSRO[OSCILLATOR_MARGIN] field description” *Table 21 (DC electrical characteristics (5.0 V, NVUSRO[PAD3V5V] = 0))*, added IPU row for $\overline{\text{RESET}}$ pin *Table 23 (DC electrical characteristics (3.3 V, NVUSRO[PAD3V5V] = 1))*, added IPU row for $\overline{\text{RESET}}$ pin *Table 33 (ADC conversion characteristics)*, added V_{INAN} entry Removed “Order codes” table *Figure 40 (Commercial product code structure)*: added a footnote updated “E = Data flash memory”
18-Sep-2013	9	Updated Disclaimer